

**Amendments to the Specification:**

Kindly replace the paragraph on page 2, lines 2-5, with the following amended paragraph:

In light of the above, there has been a proposal of adding a sintering auxiliary agent for increasing the sintering density. For example, the publication of Japanese Patent Laid Open Publication No. 2000-247739 describes an attempt of increasing the relative density to 85% to 90% by adding 0.001mol% to 0.5mol% of  $\text{Bi}_2\text{O}_3$ .

Kindly replace the paragraph on page 2, lines 20-30, with the following amended paragraph:

The present invention provides 1. A ~~a~~  $\text{SrRuO}_3$  conductive oxide sintered body characterized in that the relative density is 93% or more; 2. A conductive oxide sintered body according to paragraph 1 above, characterized in that the resistivity is  $500\mu\Omega\text{cm}$  or less; 3. A conductive oxide sintered body according to paragraph 1 above, characterized in that the resistivity is ~~or~~  $300\mu\Omega\text{cm}$  or less; 4. A The conductive oxide sintered body according to each of paragraphs 1 to 3 above, characterized in containing ~~contains~~ 0.3mol% to 1.2mol% of  $\text{Bi}_2\text{O}_3$ ; and 5. A conductive oxide sintered body according to each of paragraphs 1 to 3 above, characterized in containing ~~or~~ 0.5mol% (and above) to 1.0mol% of  $\text{Bi}_2\text{O}_3$ .

Kindly replace the paragraph on page 3, lines 1-11, with the following amended paragraph:

The present invention further provides 6. A ~~a~~ sputtering target formed from a  $\text{SrRuO}_3$  conductive oxide sintered body characterized in that the relative density is 93% or more; 7. A sputtering target formed from a  $\text{SrRuO}_3$  conductive oxide sintered body according to paragraph 6 above, characterized in that the resistivity is  $500\mu\Omega\text{cm}$  or less; 8. A sputtering target formed from a  $\text{SrRuO}_3$  conductive oxide sintered body according to paragraph 6 above, characterized in that the resistivity is ~~or~~  $300\mu\Omega\text{cm}$  or less; 9. A The sputtering target formed from a conductive oxide sintered body according to each of paragraphs 6 to 8 above, characterized in containing ~~contains~~ 0.3mol% to 1.2mol% of  $\text{Bi}_2\text{O}_3$ ; and 10. A sputtering target formed from a conductive oxide sintered body according to each of paragraphs 6 to 8 above, characterized in containing ~~or~~ 0.5mol% (and above) to 1.0mol% of  $\text{Bi}_2\text{O}_3$ .

Kindly replace the paragraph on page 3, lines 12-27, with the following amended paragraph:

The present invention additionally provides -11.-A a manufacturing method of a SrRuO<sub>3</sub> conductive oxide sintered body or a sputtering target formed from the sintered body, characterized in that 0.3mol% to 1.2mol% of Bi<sub>2</sub>O<sub>3</sub> is added as a sintering auxiliary upon manufacturing the SrRuO<sub>3</sub> conductive oxide sintered body; 12.-A manufacturing method of a SrRuO<sub>3</sub>-conductive oxide sintered body or a sputtering target formed from the sintered body, characterized in that or 0.5mol% (and above) to 1.0mol% of Bi<sub>2</sub>O<sub>3</sub> is added as a sintering auxiliary upon manufacturing the SrRuO<sub>3</sub> conductive oxide sintered body; 13.-A The manufacturing method of a SrRuO<sub>3</sub> conductive oxide sintered body or a sputtering target formed from the sintered body [,] is characterized in that sintering is performed at a sintering temperature of 1400 to 1700°C upon manufacturing the SrRuO<sub>3</sub> conductive oxide sintered body; 14.-A manufacturing method of a SrRuO<sub>3</sub>-conductive oxide sintered body or a sputtering target formed from the sintered body according to paragraph 11 or paragraph 12 above, characterized in that sintering is performed at a sintering temperature of 1400 to 1700°C upon manufacturing the SrRuO<sub>3</sub>-conductive oxide sintered body.

Kindly replace the paragraph on page 4, lines 19-23, with the following amended paragraph:

Upon manufacturing the SrRuO<sub>3</sub> conductive oxide sintered body of the present invention, 0.3mol% to 1.2mol% of Bi<sub>2</sub>O<sub>3</sub> is added as an auxiliary agent. Preferably, sintering is performed upon adding 0.5mol% (and above) to 1.0mol% of Bi<sub>2</sub>O<sub>3</sub>. Thereby, 0.3mol% to 1.2mol% of Bi<sub>2</sub>O<sub>3</sub>, preferably 0.5mol% (and above) to 1.0mol% of Bi<sub>2</sub>O<sub>3</sub> is contained in the SrRuO<sub>3</sub> conductive oxide sintered body and sputtering target.

Kindly replace the paragraph on page 4, lines 24-27, with the following amended paragraph:

In order to improve the sinterability and obtain a high density SrRuO<sub>3</sub> conductive oxide sintered body, it is necessary to added 0.3mol% or more of Bi<sub>2</sub>O<sub>3</sub>, and preferably more than 0.5mol% of Bi<sub>2</sub>O<sub>3</sub> is added. If less than 0.3mol% of Bi<sub>2</sub>O<sub>3</sub> is added, it is not possible to achieve a density of 93% or more.

Kindly replace the paragraph on page 4, line 28, to page 5, line 4, with the following amended paragraph:

However, when the  $\text{Bi}_2\text{O}_3$  contained in the  $\text{SrRuO}_3$  conductive oxide sintered body and sputtering target increases, the  $\text{Bi}_2\text{O}_3$  contained in the sputtering film will increase, and the resistivity tends to increase. Moreover, when the amount of addition exceeds 1.2mol%, a second layer is formed in the sputtering film, this generates a Bi compound at the boundary face with the BSTO film or PZT film, and causes a problem of deteriorating the dielectric property. In consideration of the above, the upper limit of the additive amount has been set to 1.2mol%, and preferably to 1.0mol%.